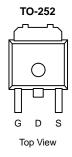
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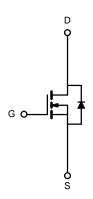
N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$V_{DS}(V)$ $r_{DS(on)}(\Omega)$				
60	0.024@ V _{GS} = 10 V	40			

FEATURES

- DT-Trench Power MOSFET
- 175°C Maximum Junction Temperature
- 100% R_g Tested





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage		V _{DS}	60	.,		
Gate-Source Voltage		V _{GS}	±20			
Continues Davis Comment /T 47500\b	T _C = 25°C	- I _D	40			
Continuous Drain Current (T _J = 175°C) ^b	T _C = 125°C		30			
Pulsed Drain Current		I _{DM}	120	A		
Continuous Source Current (Diode Conduction)		I _S	40			
Avalanche Current		I _{AR}	20			
Repetitive Avalanche Energy (Duty Cycle ≤ 1%)	L = 0.1 mH	E _{AR}	80	mJ		
	T _C = 25°C	_	136 ^b			
Maximum Power Dissipation	T _A = 25°C	P _D	₃ a	W		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 175	°C			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
	t ≤ 10 sec	R _{thJA}	15	18		
Junction-to-Ambient ^a	Steady State		40	50	°C/W	
Junction-to-Case		R _{thJC}	0.85	1.1		

a. Surface Mounted on 1" x1" FR4 Board.b. See SOA curve for voltage derating.



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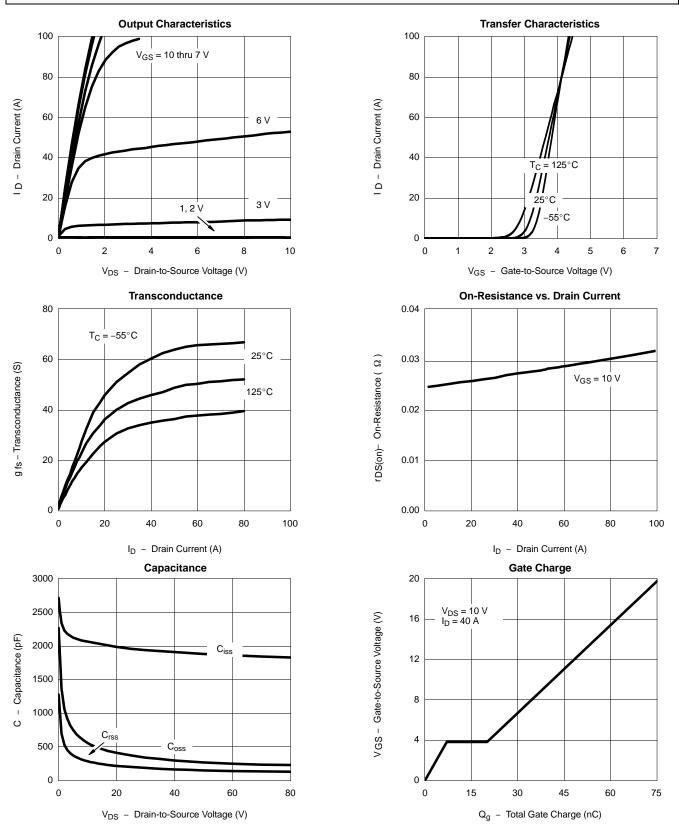
Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit	
Static	1		-	•		•	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			.,	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.0		3.0	- v	
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			±100	nA	
		V _{DS} = 60 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125^{\circ}\text{C}$			50	μА	
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$			250		
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
		$V_{GS} = 10 \text{ V}, I_D = 40 \text{ A}$	0.024		0.033		
Drain-Source On-State Resistance ^b	r _{DS(on)}	V_{GS} = 10 V, I_{D} = 40 A, T_{J} = 125°C			0.037	Ω	
		$V_{GS} = 10 \text{ V}, I_D = 40 \text{ A}, T_J = 175^{\circ}\text{C}$			0.043		
Forward Transconductance ^b	9fs	$V_{DS} = 15 \text{ V}, I_D = 40 \text{ A}$		45		S	
Dynamic ^a							
Input Capacitance	C _{iss}			1960			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, F = 1 \text{ MHz}$		370		pF	
Reverse Transfer Capacitance	C _{rss}			200			
Total Gate Charge ^c	Qg			42	60		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 40 \text{ V}, \ V_{GS} = 10 \text{ V}, \ I_D = 40 \text{ A}$		7		nC	
Gate-Drain Charge ^c	Q _{gd}			13			
Gate Resistance	R _g		0.5		2.7	Ω	
Turn-On Delay Time ^c	t _{d(on)}			12	20		
Rise Time ^c	t _r	$V_{DD} = 40 \text{ V}, R_{I} = 1.0 \Omega$		52	80		
Turn-Off Delay Time ^c	t _{d(off)}	V_{DD} = 40 V, R_L = 1.0 Ω I_D \cong 40 A, V_{GEN} = 10 V, R_g = 2.5 Ω		25	38	ns ns	
Fall Time ^c	t _f			10	15		
Source-Drain Diode Ratings an	d Characteristic	c (T _C = 25°C)					
Pulsed Current	I _{SM}				120	А	
Diode Forward Voltage ^b	V _{SD}	$I_F = 40 \text{ A}, V_{GS} = 0 \text{ V}$		1.0	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 40 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s}$		45	70	ns	

Notes a. Guaranteed by design, not subject to production testing. b. Pulse test; pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$. c. Independent of operating temperature.





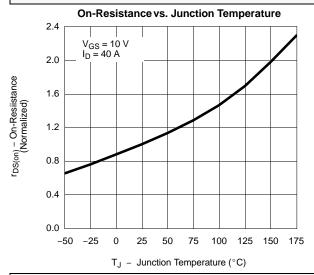
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

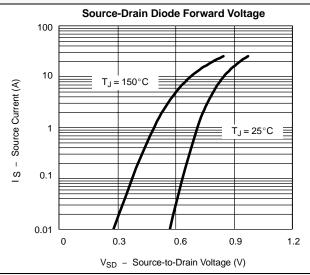




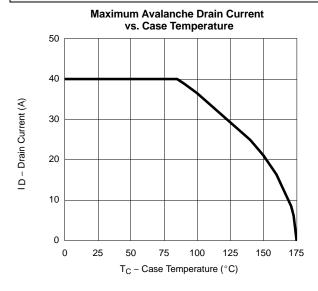
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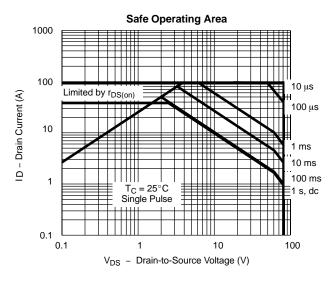
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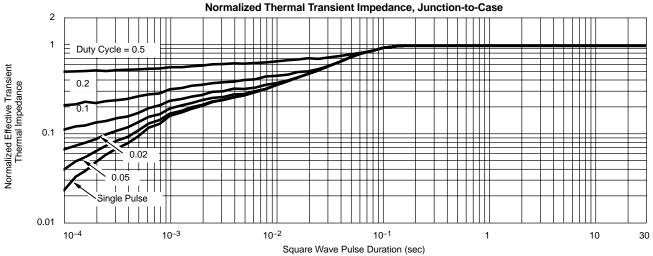




THERMAL RATINGS



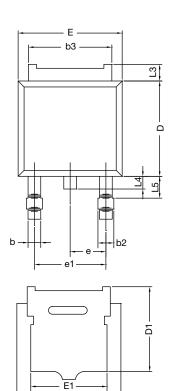


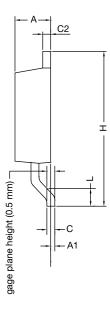






TO-252AA CASE OUTLINE





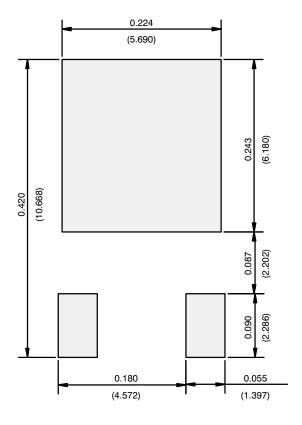
	MILLIN	METERS	INCHES			
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	5.21	-	0.205	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28	BSC	0.090 BSC			
e1	4.56 BSC		0.180 BSC			
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060		
ECN: X12-0247-Rev. M, 24-Dec-12						

DWG: 5347 Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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